

ABSTRACT

Defects in element forming regions on which memory cells of a non-volatile memory are formed are to be diminished to reduce leakage current. End portions of element forming regions with non-volatile memory cells formed thereon are extended a length D by utilizing the region which underlies a dummy conductive film, whereby a stress induced from an insulating film which surrounds the element forming regions is concentrated on the extended region. As a result, defects do not extend up to the regions where memory cells are formed and therefore it is possible to reduce leakage current in the memory cells.